

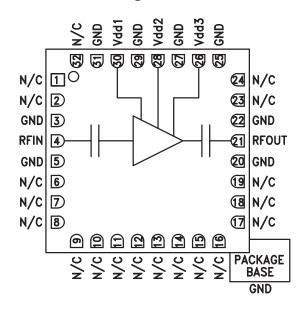
SMT PHEMT LOW NOISE AMPLIFIER, 9 - 18 GHz

Typical Applications

The HMC516LC5 is ideal for use as a LNA or driver amplifier for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- Test Equipment and Sensors
- Military

Functional Diagram



Features

Noise Figure: 2 dB

Gain: 20 dB OIP3: +25 dBm

Single Supply: +3V @ 65 mA 50 Ohm Matched Input/Output RoHS Compliant 5x5 mm Package

General Description

The HMC516LC5 is a high dynamic range GaAs pHEMT MMIC Low Noise Amplifier (LNA) housed in a leadless "Pb free" RoHS compliant SMT package. The HMC516LC5 provides 20 dB of small signal gain, 2 dB of noise figure and has an output IP3 of +25 dBm. The P1dB output power of +13 dBm enables the LNA to also function as a LO driver for balanced, I/Q or image reject mixers. The HMC516LC5 allows the use of surface mount manufacturing techniques.

Electrical Specifications, $T_{\Delta} = +25^{\circ}$ C, Vdd 1, 2, 3 = +3V

| Parameter | Min. | Тур. | Max. | Min. | Тур. | Max. | Units |
|--|------|--------|-------|------|---------|-------|--------|
| Frequency Range | | 9 - 12 | | | 12 - 18 | | GHz |
| Gain | 17.5 | 20 | | 18 | 20.5 | | dB |
| Gain Variation Over Temperature | | 0.015 | 0.025 | | 0.015 | 0.025 | dB/ °C |
| Noise Figure | | 2.0 | 2.5 | | 2.0 | 2.5 | dB |
| Input Return Loss | | 10 | | | 10 | | dB |
| Output Return Loss | | 12 | | | 12 | | dB |
| Output Power for 1 dB Compression (P1dB) | | 13 | | | 14 | | dBm |
| Saturated Output Power (Psat) | | 15 | | | 16 | | dBm |
| Output Third Order Intercept (IP3) | | 25 | | | 25 | | dBm |
| Supply Current (Idd)(Vdd = +3V) | | 65 | 88 | | 65 | 88 | mA |

HMC516LC5* PRODUCT PAGE QUICK LINKS

Last Content Update: 10/05/2017

COMPARABLE PARTS 🖵

View a parametric search of comparable parts.

EVALUATION KITS

· HMC516LC5 Evaluation Board

DOCUMENTATION

Application Notes

- AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers
- Broadband Biasing of Amplifiers General Application Note
- MMIC Amplifier Biasing Procedure Application Note
- Thermal Management for Surface Mount Components General Application Note

Data Sheet

 HMC516LC5: SMT PHEMT Low Noise Amplifier, 9 - 18 GHz Data Sheet

TOOLS AND SIMULATIONS \Box

HMC516LC5 S-Parameters

REFERENCE MATERIALS 🖵

Quality Documentation

- Package/Assembly Qualification Test Report: LC5, LC5A (QTR: 2014-00384 REV: 01)
- Semiconductor Qualification Test Report: PHEMT-A (QTR: 2013-00267)

DESIGN RESOURCES 🖵

- · HMC516LC5 Material Declaration
- PCN-PDN Information
- · Quality And Reliability
- · Symbols and Footprints

DISCUSSIONS

View all HMC516LC5 EngineerZone Discussions.

SAMPLE AND BUY 🖳

Visit the product page to see pricing options.

TECHNICAL SUPPORT 🖳

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK 🖳

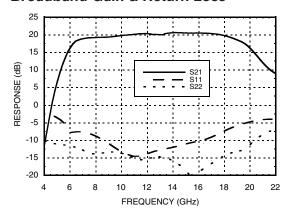
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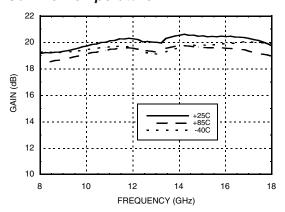


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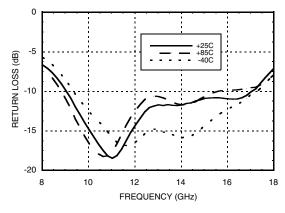
Broadband Gain & Return Loss



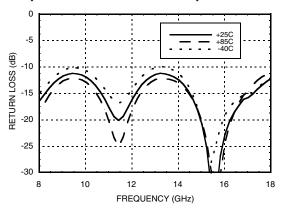
Gain vs. Temperature



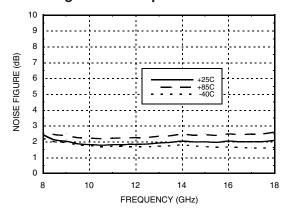
Input Return Loss vs. Temperature



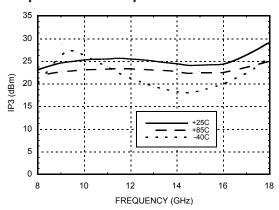
Output Return Loss vs. Temperature



Noise Figure vs. Temperature



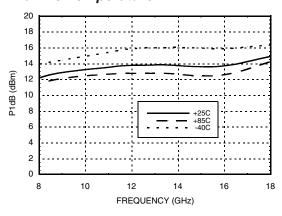
Output IP3 vs. Temperature



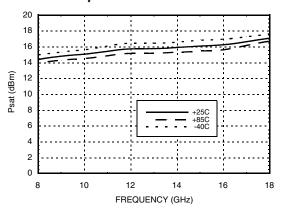


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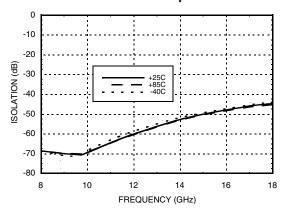
P1dB vs. Temperature



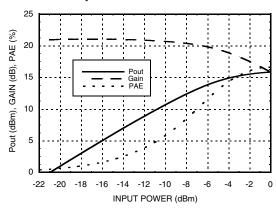
Psat vs. Temperature



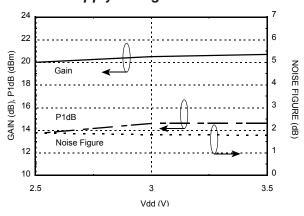
Reverse Isolation vs. Temperature



Power Compression @ 12 GHz



Gain, Noise Figure & Power vs. Supply Voltage @ 12 GHz



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SMT PHEMT LOW NOISE AMPLIFIER, 9 - 18 GHz

Absolute Maximum Ratings

| Drain Bias Voltage (Vdd1, Vdd2, Vdd3) | +4 Vdc |
|--|----------------|
| RF Input Power (RFIN)(Vdd = +3.0 Vdc) | +5 dBm |
| Channel Temperature | 175 °C |
| Continuous Pdiss (T= 85 °C) (derate 14 mW/°C above 85 °C) | 1.17 W |
| Thermal Resistance (channel to die bottom) | 76.9 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -40 to +85 °C |
| ESD Sensitivity (HBM) | Class 1A |

Typical Supply Current vs. Vdd

| Vdd (V) | Idd (mA) |
|---------|----------|
| +2.5 | 61 |
| +3.0 | 65 |
| +3.5 | 69 |

Note: Amplifier will operate over full voltage range shown above.



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Outline Drawing

BOTTOM VIEW 0.197±.005 PIN 32 .014 \[0.36 \] .009 \[0.24 \] 013 [0.32] [5.00±.13] 32 25 PIN 1 \Box 1 24 D H516 0.197±.005 [5.00±.13] \Box \Box XXXX D 0.56 \Box \Box 8 17 \Box 16 .138 [3.50] **EXPOSED** LOT NUMBER SQUARE GROUND 0.044 [1.12] .161 [4.10] PADDLE MAX **SEATING** NOTES: PLANE 1. PACKAGE BODY MATERIAL: ALUMINA -C-

- 2. LEAD AND GROUND PADDLE PLATING: 30-80 MICROINCHES GOLD OVER 50 MICROINCHES MINIMUM NICKEL
- 3. DIMENSIONS ARE IN INCHES [MILLIMETERS]
- 4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm DATUM
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND

Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking [2] |
|-------------|-----------------------|------------------|---------------------|---------------------|
| HMC516LC5 | Alumina, White | Gold over Nickel | MSL3 ^[1] | H516 XXXX |

^[1] Max peak reflow temperature of 260 °C

^{[2] 4-}Digit lot number XXXX



SMT PHEMT LOW NOISE AMPLIFIER, 9 - 18 GHz

Pin Descriptions

| Pin Number | Function | Description | Interface Schematic |
|---|------------|---|---------------------|
| 1, 2, 6 - 19, 23 - 24, 32 | GND | This pin may be connected to RF/DC ground. Performance will not be affected. | |
| 4 | RFIN | This pin is AC coupled and matched to 50 Ohms. | RFIN ○── ├── |
| 30, 28, 26 | Vdd1, 2, 3 | Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF and 2.2 μF are required. | OVdd1,2,3 |
| 21 | RFOUT | This pin is AC coupled and matched to 50 Ohms. | — —○ RFOUT |
| 3, 5, 20, 22, 25, 27, 29, 31 GND These pins and package bottom must be connected to RF/DC ground. | | = O GND | |

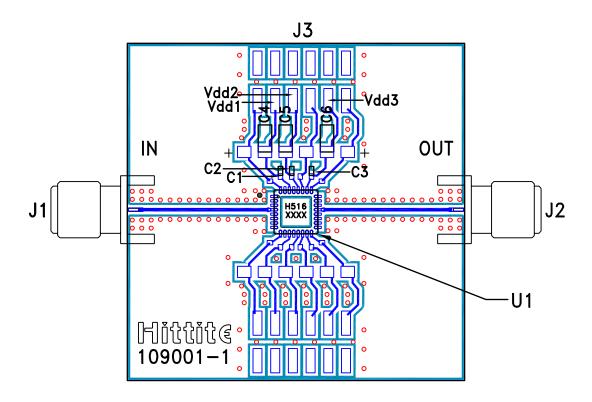
Application Circuit

| Component | Value | Vdd1 | Vdd2 | Vdd3 | |
|------------|--------|--------------|---------|-------------------------|--------------|
| C1, C2, C3 | 100 pF | φ | φ | φ | |
| C4, C5, C6 | 2.2 μF | | | | |
| | | ±C1 C4± | ±C2 C5± | <u></u> C3 C6 <u></u> | |
| | | | | | |
| | | <u>+ +</u> | + + | <u> </u> | |
| | | _ _ | _ _ | _ _ | |
| | | 30 | 20 | 26 | |
| | | 30 | 28 | 20 | |
| | | | | | |
| | | | | | |
| | | | | | |
| | | | | | |
| | RFIN | 4 | | 21 | — ✓ RFOUT |
| | KI IIV | ' | | 21 | (11 001 |
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Evaluation PCB



List of Materials for Evaluation PCB 110431 [1]

| Item | Description | |
|-------------------------------|-----------------------------|--|
| J1 - J2 | PCB Mount K Connector | |
| J3 | 2 mm DC Header | |
| C1 - C3 | 100 pF Capacitor, 0402 Pkg. | |
| C4 - C6 | 2.2 µF Capacitor, Tantalum | |
| U1 | HMC516LC5 Amplifier | |
| PCB [2] 109001 Evaluation PCB | | |

^[1] Reference this number when ordering complete evaluation PCB $\,$

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Analog Devices, upon request.

^[2] Circuit Board Material: Rogers 4350